

Patent Assignment Abstract of Title

Total Assignments: 2

Application #: 09184490 **Filing Dt:** 11/02/1998 **Patent #:** 6325858 **Issue Dt:** 12/04/2001

PCT #: NONE

Publication #: NONE

Pub Dt:

Inventors: JOHN F. WENGERT, IVO RAAIJMAKERS, MIKE HALPIN, LOREN JACOBS, MICHAEL J. MEYER, FRANK VAN BILSEN, MATT GOODMAN, ERIC BARRETT, ERIC WOOD, BLAKE SAMUELS

Title: LONG LIFE HIGH TEMPERATURE PROCESS CHAMBER

Assignment: 1

Reel/Frame: 010881/0362 **Received:** 07/14/2000 **Recorded:** 06/13/2000 **Mailed:** 08/22/2000 **Pages:** 15

Conveyance: CHANGE OF NAME (SEE DOCUMENT FOR DETAILS).

Assignor: ADVANCED SEMICONDUCTOR MATERIALS AMERICA, INC. **Exec Dt:** 12/12/1997

Assignee: ASM AMERICA, INC.

3440 EAST UNIVERSITY DRIVE
PHOENIX, ARIZONA 85034

Correspondent: KNOBBE, MARTENS, OLSON & BEAR, LLP
GORDON H. OLSON
SIXTEENTH FLOOR
620 NEWPORT CENTER DRIVE
NEWPORT BEACH, CA 92660

Assignment: 2

Reel/Frame: 009701/0741 **Received:** 01/21/1999 **Recorded:** 01/20/1999 **Mailed:** 04/17/1999 **Pages:** 8

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors: WENGERT, JOHN F.

Exec Dt: 11/19/1998

RAAIJMAKER, IVO

Exec Dt: 10/23/1998

HALPIN, MIKE

Exec Dt: 11/16/1998

JACOBS, LOREN

Exec Dt: 10/29/1998

MEYER, MICHAEL J.

Exec Dt: 10/29/1998

VAN BILSEN, FRANK

Exec Dt: 10/29/1998

GOODMAN, MATT

Exec Dt: 10/29/1998

BARRETT, ERIC

Exec Dt: 10/29/1998

WOOD, ERIC

Exec Dt: 10/29/1998

SAMUELS, BLAKE

Exec Dt: 12/02/1998

Assignee: ADVANCED SEMICONDUCTOR MATERIALS AMERICA, INC.

3440 EAST UNIVERSITY DRIVE
PHOENIX, ARIZONA 85034

Correspondent: KNOBBE, MARTENS, OLSON & BEAR, LLP
GORDON H. OLSON
SIXTEENTH FLOOR
620 NEWPORT CENTER DRIVE
NEWPORT BEACH, CA 92660

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Web interface last modified: Oct. 5, 2002

Patent Assignment Abstract of Title

Total Assignments: 1

Application #: 09439833 **Filing Dt:** 11/12/1999 **Patent #:** 6342691 **Issue Dt:** 01/29/2002

PCT #: NONE

Publication #: NONE

Pub Dt:

Inventors: KRISTIAN E. JOHNSGARD, JEAN-FRANCOIS DAVIET, JAMES A. GIVENS, STEPHEN E. SAVAS, BRAD S. MATTSON, ASHUR J. ATANOS

Title: APPARATUS AND METHOD FOR THERMAL PROCESSING OF SEMICONDUCTOR SUBSTRATES

Assignment: 1

Reel/Frame: 010709/0817 **Received:** 04/24/2000 **Recorded:** 04/14/2000 **Mailed:** 06/20/2000 **Pages:** 2

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors: JOHNSGARD, KRISTIAN E.

Exec Dt: 04/12/2000

DAVIET, JEAN-FRANCOIS

Exec Dt: 03/24/2000

GIVENS, JAMES A.

Exec Dt: 04/10/2000

SAVAS, STEPHEN E.

Exec Dt: 03/06/2000

MATTSON, BRAD S.

Exec Dt: 03/31/2000

ATANOS, ASHUR J.

Exec Dt: 04/12/2000

Assignee: MATTSON TECHNOLOGY, INC.

3550 WEST WARREN AVENUE
FREMONT, CALIFORNIA 94538

Correspondent: WILSON SONSINI GOODRICH & ROSATI

MICHAEL J. MURPHY
SR 1-2
650 PAGE MILL ROAD
PALO ALTO, CA 94304-1050

Search Results as of: 1/9/2003 11:36:26 A.M.

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Web interface last modified: Oct. 5, 2002

Patent Assignment Abstract of Title

Total Assignments: 1

Application #: 09828550 **Filing Dt:** 04/06/2001

Patent #: NONE

Issue Dt:

PCT #: NONE

Publication #: 20020011211

Pub Dt: 01/31/2002

Inventor: Michael W. Halpin

Title: Barrier coating for vitreous materials

Assignment: 1

Reel/Frame: 011687/0225 **Received:**
04/20/2001

Recorded:
04/06/2001

Mailed:
07/02/2001

Pages: 2

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignor: HALPIN, MICHAEL W.

Exec Dt: 04/06/2001

Assignee: ASM AMERICA, INC.

3440 EAST UNIVERSITY DRIVE
PHOENIX, ARIZONA 85034

Correspondent: KNOBBE, MARTENS, OLSON & BEAR, LLP

GORDON H. OLSON
SIXTEENTH FLOOR
620 NEWPORT CENTER DRIVE
NEWPORT BEACH, CALIFORNIA 92660

Search Results as of: 1/9/2003 11:35:46 A.M.

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Web interface last modified: Oct. 5, 2002

L Number	Hits	Search Text	DB	Time stamp
1	2	6342691.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:46
8	32	((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:54
15	1	(quartz or 'SiO.sub.2') and ("silicon nitride" or 'Si.sub.3 N.sub.4') and (((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347"))).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:04
22	0	6120640.pn. and sputter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:43
29	0	6120640.pn. and sputt\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:45
36	0	5910221.pn. and sputt\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:44
43	2	6120640.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:51
50	3349	(Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:14
57	1904	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:59
64	475	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15
71	33	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:00
78	442	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))) not (((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:04
85	181	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))) not (((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5)) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15

92	35	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom)) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:13
99	291	(Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:18
106	53	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15
113	20	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
120	271	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
127	9	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank))) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
134	464	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect\$4 or prevent\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:21
141	5	((Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect\$4 or prevent\$4)) and (118/\$.ccls. or 156/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
148	1	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
155	43	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:27
162	2	((Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall) and (118/\$.ccls. or 156/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
169	51	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) and 118/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:28

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8	32	((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:54
15	1	(quartz or 'SiO.sub.2') and ("silicon nitride" or 'Si.sub.3 N.sub.4') and (((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347"))).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:04